Evolution of Threading Dislocations in GaN Films Grown on (111) Si Substrates with Various Buffer Layers

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Compared to commonly used sapphire and SiC, (111) Si offers several advantages as a substrate for Group-III nitride growth including high quality, low cost, large wafer size, and the potential integration of nitride devices with Si microelectronics. Therefore, growth of GaN on (111) Si is of great interest at the present time. In order to prevent the reaction between Ga and Si and improve the wetting properties of the film, a thin (~100 nm) AlN layer is often used as the buffer between the GaN film and the Si substrate. Due to the tensile coefficient of thermal expansion (CTE) mismatch stress and the additional tensile growth stress arising from island coalescence and lateral grain growth, cracks often form in thick (>~250 nm) GaN films grown on Si using thin AlN buffer layers. For example, a crack is evident in Fig. 1 (a), a bright-field cross-sectional transmission electron microscopy (TEM) image of a GaN/Si heterostructure with a thin AlN buffer layer. By using a compositionally graded Al_{1-x}Ga_{x}N buffer layer instead of the AlN buffer, a compressive lattice mismatch stress can be induced to offset the tensile CTE mismatch stress and growth stress, thus suppressing the cracking [1-4]. In this work, the effects of Al_{1-x}Ga_{x}N buffer layers and Al_{1-x}Ga_{x}N/GaN/AlN buffer combinations on the evolution of threading dislocations (TDs) in GaN films are studied.

Figure 1 (b) is a cross-sectional TEM image of a 500 nm GaN film grown on a 1 µm Al_{1-x}Ga_{x}N buffer layer, collected under the multi-beam diffraction condition to reveal all types of TDs. It is evident that significant bending and annihilation of TDs occur in the top half of the Al_{1-x}Ga_{x}N buffer layer. The TD densities of the GaN films were determined using plan-view TEM images collected from 10 different regions with a total area of ~20 µm². Figures 2 (a) and (b) are typical plan-view images for GaN films grown directly on thin AlN buffers and on Al_{1-x}Ga_{x}N buffer layers, respectively. A reduced TD density of (1.1±0.2)×10¹⁰ cm⁻² in GaN films grown on Al_{1-x}Ga_{x}N buffer layers was achieved, in comparison with (1.5±0.3)×10¹⁰ cm⁻² for those grown directly on AlN buffer layers. This TD density reduction is apparently due to the bending and annihilation of TDs in the compositionally graded Al_{1-x}Ga_{x}N buffer layer shown in Fig. 1 (b).

Due to the high lattice mismatch (-19% for x=0 at the interface) between the Al_{1-x}Ga_{x}N buffer layer and the Si substrate, the initial TD density in the Al_{1-x}Ga_{x}N buffer layer near the Al_{1-x}Ga_{x}N/Si interface is very high. This is illustrated in Fig. 1 (b), where individual TDs cannot be distinguished near the buffer/Si interface. Reducing this initial TD density in the Al_{1-x}Ga_{x}N buffer layer may further reduce the TD density in the overgrown GaN film. Thus, an AlN buffer and a GaN base layer were grown before the growth of the compositionally graded Al_{1-x}Ga_{x}N buffer layer in order to reduce the lattice mismatch and the initial TD density in the Al_{1-x}Ga_{x}N layer. Figure 1 (c) shows a cross-sectional TEM image of the Al_{1-x}Ga_{x}N/GaN/AlN buffer combination. Clearly, the initial TD density in the Al_{1-x}Ga_{x}N buffer layer near the Al_{1-x}Ga_{x}N/GaN interface is significantly lower than that near the Al_{1-x}Ga_{x}N/Si interface shown in Fig. 1 (b), as a result of the much lower lattice mismatch (-2.5% at x=0) between Al_{1-x}Ga_{x}N and GaN than that between Al_{1-x}Ga_{x}N and Si. Figure 2
(c) is a typical plan-view TEM image of a GaN film grown on such an Al$_{1-x}$Ga$_x$N/GaN/AlN buffer combination. The TD density of this GaN film is $(6.1 \pm 1.4) \times 10^9$ cm$^{-2}$, ~45% lower than that grown on a single Al$_{1-x}$Ga$_x$N buffer layer.

References


Fig. 1. Bright-field cross-sectional TEM images of GaN/Si heterostructures with (a) a thin AlN buffer layer, (b) a linearly graded Al$_{1-x}$Ga$_x$N buffer layer, and (c) an AlN/GaN/AlGaN buffer combination. All the images were collected under multi-beam diffraction condition near the GaN $[0001]$ zone axis. The dashed line in (b) indicates the approximate position of the GaN/ Al$_{1-x}$Ga$_x$N interface.

Fig. 2. Bright-field plan-view TEM images of GaN film grown on (a) a thin AlN buffer layer, (b) a linearly graded Al$_{1-x}$Ga$_x$N buffer layer, and (c) a buffer combination. All the images were collected under multi-beam diffraction condition near the GaN $[0001]$ zone axis.